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April 2013

FDT3N40

N-Channel UniFET[™] MOSFET 400 V, 2.0 A, 3.4

Features

- $R_{DS(on)} = 3.4 \Omega \text{ (Max.)} @ V_{GS} = 10 \text{ V}, I_D = 1.0 \text{ A}$
- Low Gate Charge (Typ. 4.5 nC)
- Low Crss (Typ. 3.7 pF)
- 100% Avalanche Tested

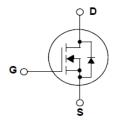
Applications

- LCD/LED TV
- Lighting
- Uninterruptible Power Supply

Description

UniFET™ MOSFET is Fairchild Semiconductor®'s high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.





Absolute Maximum Ratings

Symbol	Parameter		FDT3N40	Unit	
V _{DSS}	Drain-Source Voltage		400	V	
I _D	Drain Current	- Continuous (T _C = 25°C - Continuous (T _C = 100°		2.0 * 1.2 *	A A
I _{DM}	Drain Current	- Pulsed	(Note 1)	8.0 *	А
V _{GSS}	Gate-Source voltage		±30	V	
E _{AS}	Single Pulsed Avalanche Energy		(Note 2)	46	mJ
I _{AR}	Avalanche Current		(Note 1) 2		A
E _{AR}	Repetitive Avalanche Energy		(Note 1)	0.2	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		(Note 3)	4.5	V/ns
P _D	Power Dissipation (T _C = 25°C) - Derate above 25°C			2 0.02	W W/°C
T _{J,} T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C	
T _L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds		300	°C	

^{*} Drain current limited by maximum junction temperature

Thermal Characteristics

Symbol	Parameter	FDT3N40	Unit
$R_{\theta JA}^{ *}$	Thermal Resistance, Case-to-Sink Typ.	60	°C/W

Surface Mounted on JESD51-3 Board, T<0.1sec.

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDT3N40	FDT3N40TF	SOT-223	330mm	12mm	4000

Electrical Characteristics $T_C = 25$ °C unless otherwise noted

Symbol	Parameter	Conditions	Min.	Тур.	Max	Unit
Off Charac	Off Characteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_{D} = 250\mu A$	400			V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250μA, Referenced to 25°C		0.4		V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 400V, V _{GS} = 0V V _{DS} = 320V, T _C = 125°C			1 10	μA μA
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30V, V _{DS} = 0V			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -30V$, $V_{DS} = 0V$			-100	nA
On Charac	teristics	•				
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	3.0		5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10V, I _D = 1A		2.8	3.4	Ω
9 _{FS}	Forward Transconductance	$V_{DS} = 40V$, $I_D = 1A$ (Note 4)		2		S
Dynamic C	haracteristics	•				
C _{iss}	Input Capacitance	V _{DS} = 25V, V _{GS} = 0V,		173	225	pF
C _{oss}	Output Capacitance	f = 1.0MHz		30	40	pF
C _{rss}	Reverse Transfer Capacitance			3.7	6	pF
Switching	Characteristics					
t _{d(on)}	Turn-On Delay Time	$V_{DD} = 200V, I_{D} = 2A$		10	30	ns
t _r	Turn-On Rise Time	$R_G = 25\Omega$		30	70	ns
t _{d(off)}	Turn-Off Delay Time			10	30	ns
t _f	Turn-Off Fall Time	(Note 4, 5)		25	60	ns
Qg	Total Gate Charge	V _{DS} = 320V, I _D = 2A		4.5	6	nC
Q_{gs}	Gate-Source Charge	V _{GS} = 10V		1.2		nC
Q_{gd}	Gate-Drain Charge	(Note 4, 5)		2		nC
Drain-Sour	ce Diode Characteristics and Maximur	n Ratings				
I _S	Maximum Continuous Drain-Source Diode Forward Current				2	Α
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current				8	Α
V_{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0V, I _S = 2A			1.4	V
t _{rr}	Reverse Recovery Time	$V_{GS} = 0V$, $I_S = 2A$		210		ns
Q _{rr}	Reverse Recovery Charge	$dI_F/dt = 100A/\mu s (Note 4)$		0.75		μС

NOTES

^{1.} Repetitive Rating: Pulse width limited by maximum junction temperature

^{2.} L = 10mH, I $_{AS}$ = 2A, V $_{DD}$ = 50V, R $_{G}$ = 25 Ω , Starting T $_{J}$ = 25°C

^{3.} I_{SD} \leq 2A, di/dt \leq 200A/µs, V_{DD} \leq BV_DSS, Starting T_J = 25°C

^{4.} Pulse Test: Pulse width $\leq 300 \mu \text{s}, \ \text{Duty Cycle} \leq 2\%$

 $^{{\}bf 5.} \ {\bf Essentially} \ {\bf Independent} \ {\bf of} \ {\bf Operating} \ {\bf Temperature} \ {\bf Typical} \ {\bf Characteristics}$

Typical Performance Characteristics

Figure 1. On-Region Characteristics

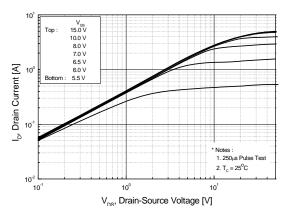


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

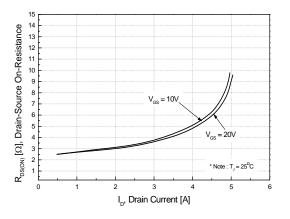


Figure 5. Capacitance Characteristics

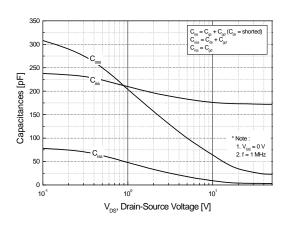


Figure 2. Transfer Characteristics

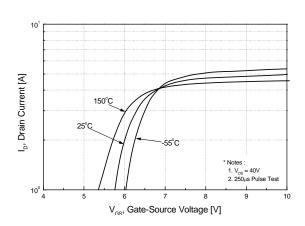


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperatue

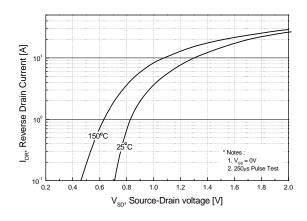
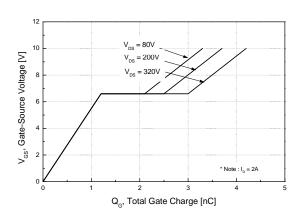


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

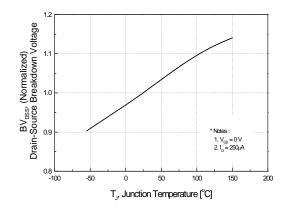


Figure 8. On-Resistance Variation vs. Temperature

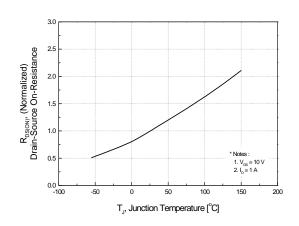
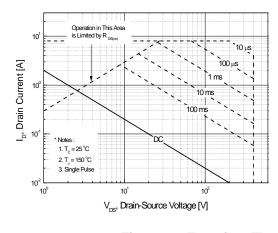


Figure 9. Maximum Safe Operating Area

Figure 10. Maximum Drain Current vs. Case Temperature



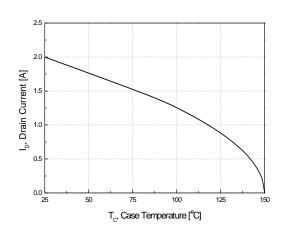
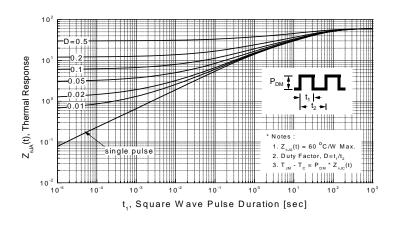
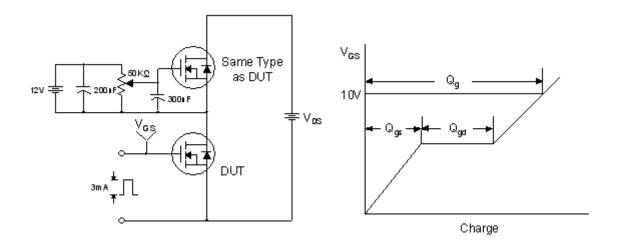


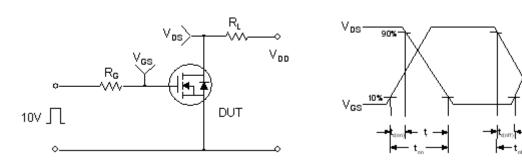
Figure 11. Transient Thermal Response Curve



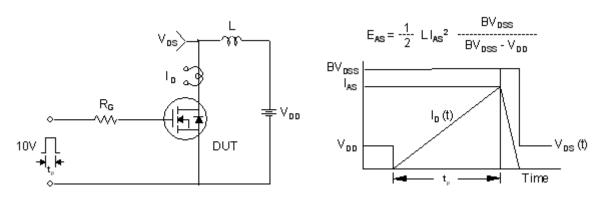
Gate Charge Test Circuit & Waveform



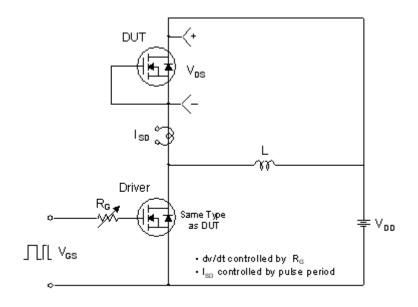
Resistive Switching Test Circuit & Waveforms

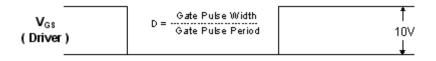


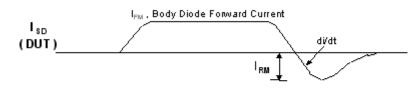
Unclamped Inductive Switching Test Circuit & Waveforms

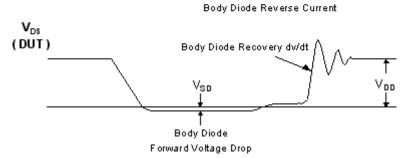


Peak Diode Recovery dv/dt Test Circuit & Waveforms



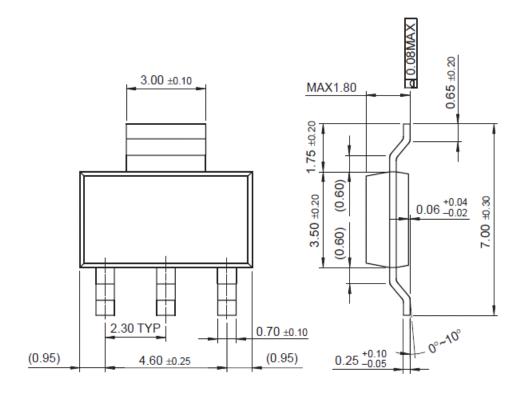


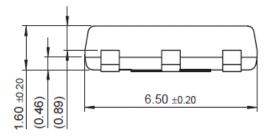




Mechanical Dimensions

SOT-223









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